

N-Channel Enhancement Mode MOSFET

1. Product Information

Features

Self-aligned planar Technology

Improve switching performance

Pin Description

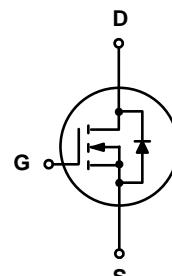
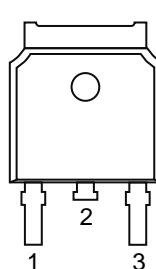
Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

Applications

Uninterruptible Power Supply (UPS)

Power Factor Correction (PFC)

Simplified Outline Symbol



Top View
TO-252

Quick reference

$V_{DS} = 200V$

$I_D = 18A$

$R_{DS(ON)} < 150m\Omega$ @ $V_{GS} = 10 V$ (Type:120mΩ)

Package Marking and Ordering Information

Product Name	Package	Marking	Reel Size	Tape width	Quantity	
KJ18N20KH	TO-252	18N20 XXXXYY	XXXYYY: Date Code	-	-	2500

2. Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage ($V_{GS}=0V$)	200	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	18	A
I_{DM}	Pulsed Drain Current ¹	72	A
E_{AS}	Single Pulse Avalanche Energy ²	340	mJ
I_{AS}	Avalanche Current ¹	15	A
E_{AR}	Repetitive Avalanche Energy ¹	8.3	mJ
P_D	Power Dissipation @ $T_c=25^\circ C$	104	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55~150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-to-Case	1.2	°C/W

3. Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$, $I_{\text{D}}=250\mu\text{A}$	200	220	-	V
I_{GSS}	Gate-body Leakage current	$V_{\text{DS}}=0\text{V}$, $V_{\text{GS}}=\pm 20\text{V}$	-	-	± 100	nA
$I_{\text{DS}}^{\text{SS}}$	Zero Gate Voltage Drain Current, $T_J=25^\circ\text{C}$	$V_{\text{DS}}=200\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	5	μA
$I_{\text{DS}}^{\text{SS}}$	Zero Gate Voltage Drain Current, $T_J=125^\circ\text{C}$	$V_{\text{DS}}=160\text{V}$, $V_{\text{GS}}=0\text{V}$	-	-	100	
$V_{\text{GS}(\text{th})}$	Gate-Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}$, $I_{\text{D}}=250\mu\text{A}$	2.0	3.5	4.0	V
$R_{\text{DS}(\text{on})}$	Drain-Source on-Resistance ³	$V_{\text{GS}}=10\text{V}$, $I_{\text{D}}=9\text{A}$	-	120	150	$\text{m}\Omega$
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$, $V_{\text{DS}}=25\text{V}$, Frequency=1MHz	-	1318	-	pF
C_{oss}	Output Capacitance		-	180	-	
C_{rss}	Reverse Transfer Capacitance		-	75	-	
Q_g	Total Gate Charge	$V_{\text{GS}}=10\text{V}$ $V_{\text{DS}}=160\text{V}$ $I_{\text{D}}=18\text{A}$	-	41	-	nC
Q_{gs}	Gate-Source Charge		-	5.5	-	
Q_{gd}	Gate-Drain Charge		-	19.5	-	
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DD}}=100\text{V}$ $R_{\text{G}}=25\Omega$ $I_{\text{D}}=18\text{A}$	-	24	-	ns
t_r	Turn-on Rise Time		-	45	-	
$t_{\text{d}(\text{off})}$	Turn-off Delay Time		-	101	-	
t_f	Turn-off Fall Time		-	95	-	
I_s	Continuous Source Current	$T_c=25^\circ\text{C}$	-	-	18	A
I_{SM}	Pulsed Diode Forward Current		-	-	72	
V_{SD}	Diode Forward Voltage	$T_J=25^\circ\text{C}$, $I_{\text{SD}}=18\text{A}$, $V_{\text{GS}}=0\text{V}$	-	-	1.4	V
t_{rr}	Body Diode Reverse Recovery Time	$V_{\text{GS}}=0\text{V}$, $I_s=18\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$	-	230	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1.8	-	μC

Notes:

- 1、The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2、The EAS data shows Max. rating. $I_{\text{AS}}=15\text{A}$, $V_{\text{DD}}=50\text{V}$, $R_{\text{G}}=25\Omega$, Starting $T_J=25^\circ\text{C}$
- 3、The test condition is Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$
- 4、The power dissipation is limited by 150°C junction temperature
- 5、The data is theoretically the same as I_{D} and I_{DM} , in real applications , should be limited by total power dissipation.

4. Typical Characteristics

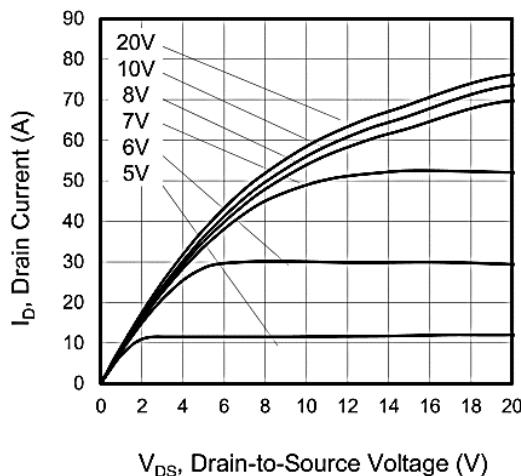


Figure1: Output Characteristics ($T_J=25^{\circ}\text{C}$)

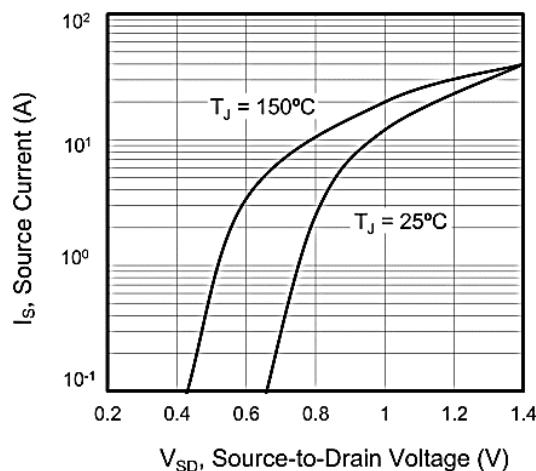


Figure 2: Body Diode Forward Voltage

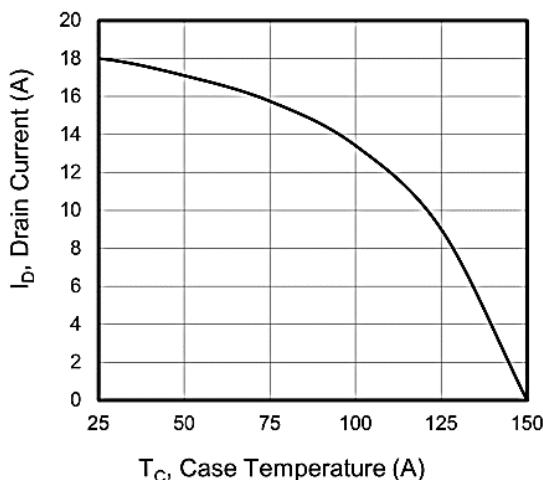


Figure 3: Drain Current vs. Temperature

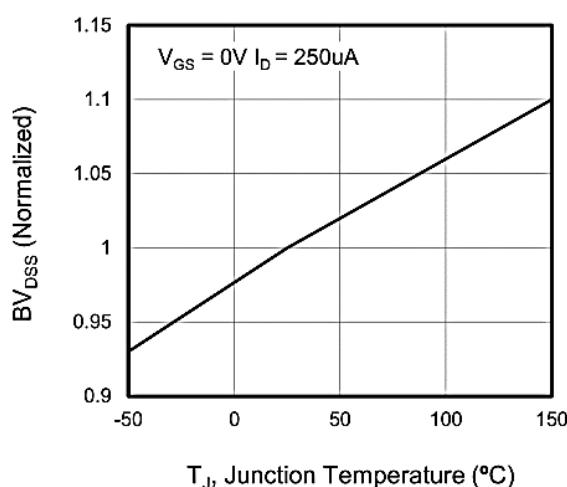


Figure 4: Body Diode Characteristics

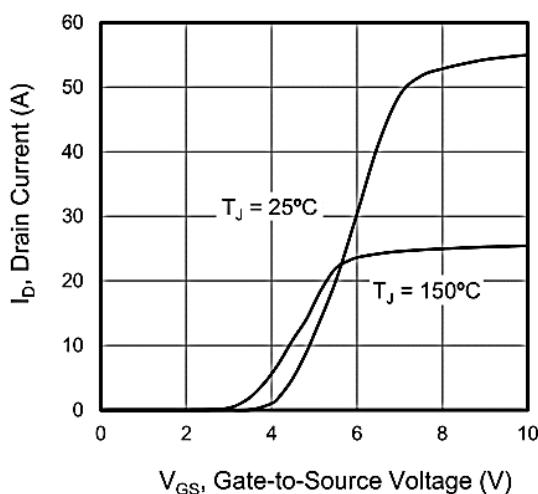


Figure 5: Transfer Characteristics

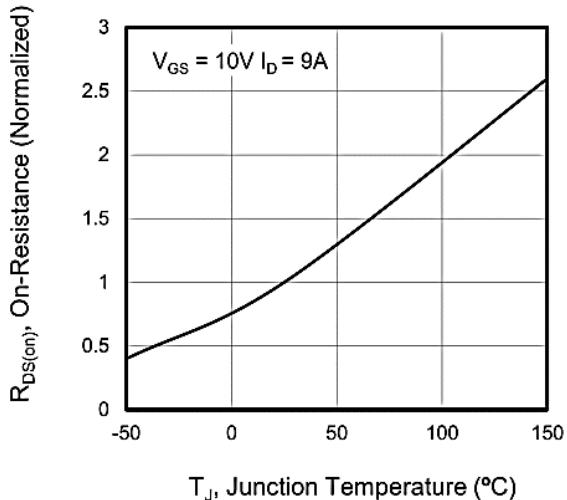
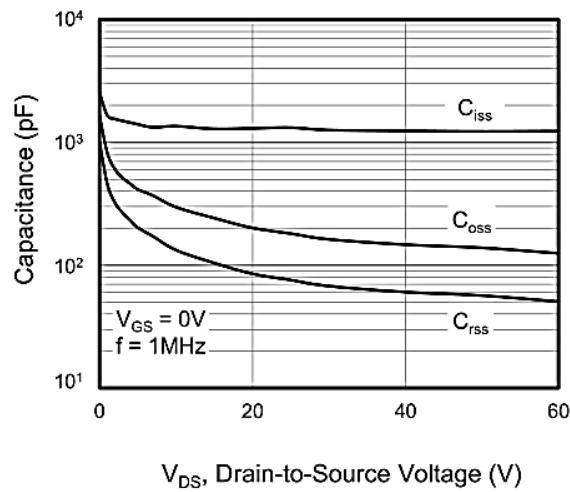


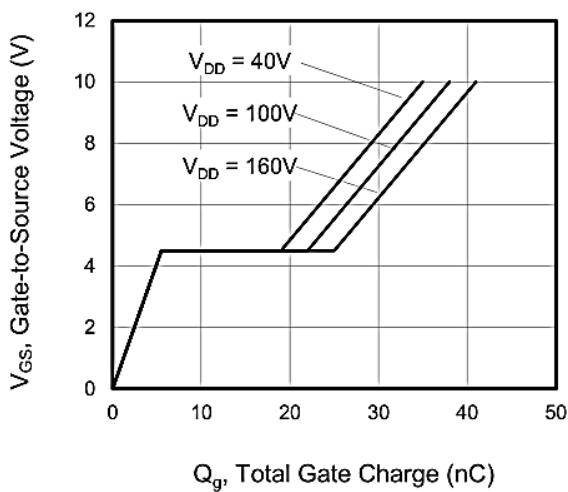
Figure 6: On-resistance vs. Temperature

4. Typical Characteristics (cont.)



V_{DS}, Drain-to-Source Voltage (V)

Figure 7: Capacitance



Q_g , Total Gate Charge (nC)

Figure 8: Gate Charge

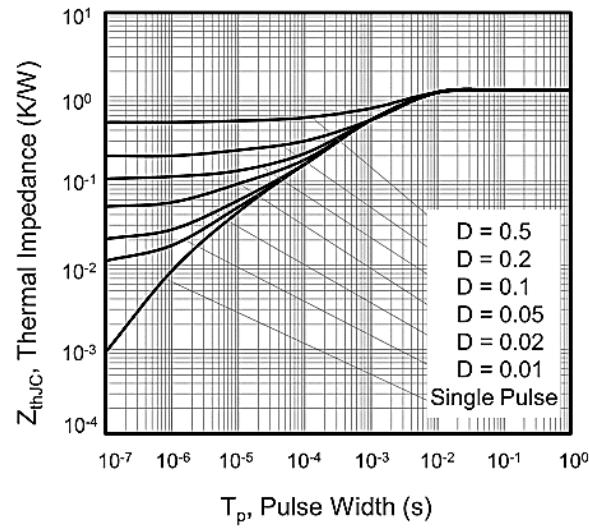
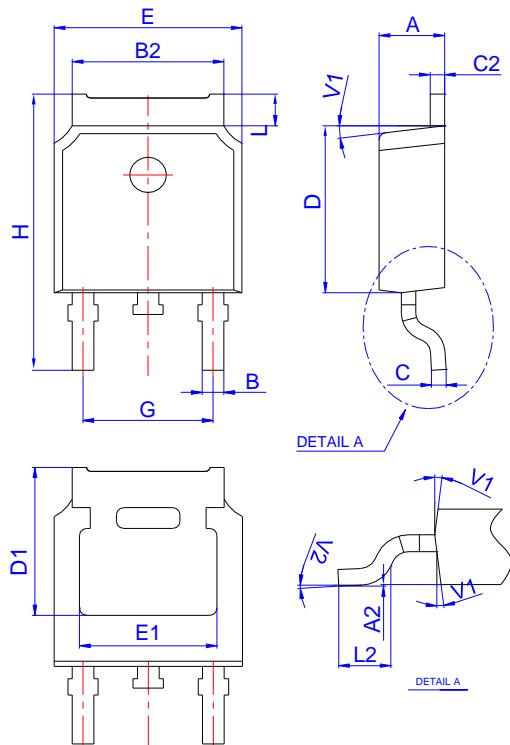


Figure 9: Transient Thermal Impedance

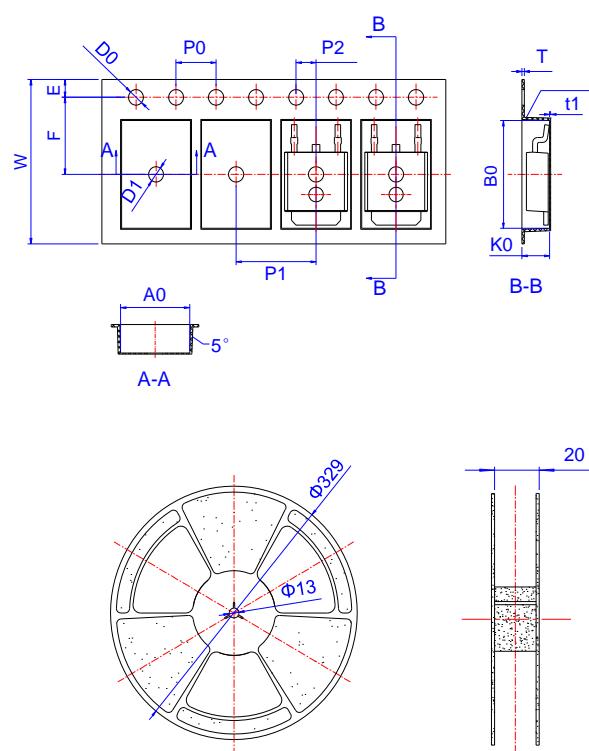
5. Package Mechanical Data

TO-252 Package



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.1		2.5	0.083		0.098
A2	0		0.1	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.4		0.6	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.9		6.3	0.232		0.248
D1	5.30REF			0.209REF		
E	6.4		6.8	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.5		10.7	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.9	16	16.1	0.626	0.63	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.4	7.5	7.6	0.291	0.295	0.299
D0	1.4	1.5	1.6	0.055	0.059	0.063
D1	1.4	1.5	1.6	0.055	0.059	0.063
P0	3.9	4	4.1	0.154	0.157	0.161
P1	7.9	8	8.1	0.311	0.315	0.319
P2	1.9	2	2.1	0.075	0.079	0.083
A0	6.85	6.9	7	0.27	0.271	0.276
B0	10.45	10.5	10.6	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24			0.09		0.011
t1	0.1			0.004		
10P0	39.8	40	40.2	1.567	1.575	1.583